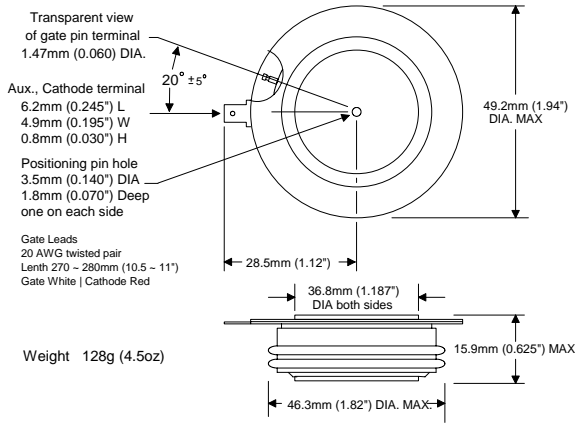


GA package



Part number scheme

GA T 07 N 18 KNX
1 2 3 4 5 6

- 1) Package designation
- 2) Thyristor designation (i.e. SCR)
- 3) Series number
- 4) Designates standard recovery time
- 5) Voltage Multiplier (example: 18 x 100 = 1800)
- 6) Proprietary suffix

Features:

- ✓ All diffused silicone.
- ✓ Center amplifying gate.
- ✓ Standard recovery time for phase control applications.
- ✓ Disk press package (nick named, Hockey Puck)
- ✓ Metal and ceramic package construction.
- ✓ Double side cooling.

Voltage

| Parameter | Symbol | Rating | Units |
|---|------------------------------------|------------------------------------|--|
| Maximum Repetitive Off-State Voltage <small>Notes: 1, 3, 4, 5, 6, 7</small> | V _{DRM} | 1600 ~ 2600 | Volts |
| Maximum Repetitive Reverse Voltage <small>Notes: 1, 3, 4, 5, 6</small> | V _{RRM} | 1600 ~ 2700 | Volts |
| Maximum non repetitive Surge of Reverse Voltage <small>Notes: 2, 3, 4, 5, 6</small> | V _{RSM} | V _{RRM} + 100 | Volts |
| Critical rate of rising off-state Voltage, Linear to 80% of V _{DRM} <small>Note: 2</small> | dv/dt | 200 | V/μs |
| <small>Note 1: T_J 25°C. Note 2: T_J 125°C. Note 3: Measured at the peak of the sine wave, Note 4: Below 0°C derate V_{DRM} and V_{RRM} 10%. Note 5: V_{DRM} and V_{RRM} have I_{DRM}, I_{RRM} of up to 35mA. Note 6: V_{DR} and V_{RR} have typical I_{DR}, I_{RR} of 2~7mA. Note 7: For DC applications derate V_{DRM} 45%.</small> | | | |
| Specifying voltage: | 1800V, GAT07N18 1600V, GAT07N16 | 2200V, GAT07N22 2400V, GAT07N24 | 2600V, GAT07N26 Above 2600V inquire for availability. |

Gate

| Parameter | Symbol | Rating | | | Units |
|--|----------------------|------------------------|-------------------------------------|------|---------|
| | | Temp. | Typ. | Max. | |
| Gate Trigger Voltage <small>Note 3</small> | V _{GT} | -20°C 25°C 125°C | 2.7 ~ 3.5 2.6 ~ 3.3 2.5 ~ 3.1 | 3.5 | Volts |
| Maximum Gate Trigger Current <small>Notes 1,3</small> | I _{GT} | | 300 | | mA |
| Minimum Forward Current to Latch on-state <small>Notes 1, 5</small> | I _L | | 800 | | mA |
| Maximum permissible Gate Voltage not to Trigger <small>Notes 1,3</small> | V _{GDM} | | 250 | | mV |
| Maximum permissible Gate Current not to Trigger <small>Notes 1, 3</small> | I _{GDM} | | 10 | | mA |
| Maximum peak non repetitive Gate Voltage <small>Notes 2, 3</small> | V _{GM} | | 8.4 | | Volts |
| Maximum Negative Gate Voltage <small>Notes 2, 4</small> | -V _{GM} | | 5 | | Volts |
| Maximum non repetitive Gate Current <small>Notes 2, 3</small> | I _{GM} | | 3.7 | | Amperes |
| Maximum Repetitive Gate Current <small>Notes 2, 3</small> | I _{GRM} | | 1 | | Amperes |
| Average Gate Power (recommended) <small>Note 2, 3</small> | P _{GI(AVE)} | | 0.9 ~ 3 | | Watts |
| <small>Note 1: T_J 25°C. Note 2: T_J 125°C. Note 3: Rectangular pulse, t_p ≤ 8.3 ms. Note 4: Rectangular -V_{DC} pulse, t_p ≤ 8.3 ms. Note 5: Test conditions: I_{DC} R_L = 12Ω.</small> | | | | | |

Amperage

| Parameter | Symbol | Rating | Units |
|---|--|-----------------|-----------------|
| Maximum, Average, On state, Current <small>Notes: 3, 4</small> | I _{T(AVE)} | 750 | Amperes |
| Maximum, RMS, On state, Current <small>Notes: 3, 5</small> | I _{T(RMS)} | 1100 | Amperes |
| Maximum non repetitive, Surge, On state, Current, with no reverse voltage reapplied. <small>Notes: 2, 4</small> | I _{TSM} 0% V _{RRM} | 9 | kA |
| Maximum non repetitive, Surge, On state, Current, with maximum reverse voltage reapplied. <small>Notes: 2, 4</small> | I _{TSM} 100% V _{RRM} | 8 | kA |
| Critical rate of rising On-state Current, non repetitive <small>Note: 6, 7</small> | di/dt | 400 | A/μs |
| Holding Current <small>Notes: 1, 5</small> | I _H | 400 | mA |
| I _{DR} = Repetitive, Off-State, leakage Current (typical) <small>Note: 1</small> I _{RR} = Repetitive, Reverse, leakage Current. (typical) <small>Note: 1</small> | I _{DR} & I _{RR} | 2 ~ 7 | mA |
| I _{DRM} = Maximum (threshold), Repetitive, Off-State, Current. <small>Note: 1</small> I _{RRM} = Maximum (threshold), Repetitive, Reverse, Current. <small>Note: 1</small> | I _{DRM} & I _{RRM} | 35 | mA |
| Fuse's absolute maximum I ² t with no reverse voltage reapplied <small>Note: 2, 4</small> | I ² t, 0% V _{RR} | 265 | kA |
| Fuse's absolute maximum I ² t with up to 80% of V _{RRM} reapplied <small>Note: 2, 4</small> | I ² t, ≤ 80% V _{RRM} | 187 | kA |
| Reverse Recovery Charge (C _S = Stored Charge) | Q _{RR} | Consult factory | μC _S |
| <small>Note 1: T_J 25°C. Note 2: T_J 125°C. Note 3: T_{Case} 55°C, double side air cooled. Note 4: 180° conduction, 60Hz sine wave. Note 5: Test conditions: I_{DC} R_L = 12Ω. Note 6: Switching from V_{DRM} ≤ 1000V. Note 7: In addition to 0.2μF and 20Ω snubber circuit</small> | | | |

Thermal & Mechanical

| Parameter | Symbol | Rating | Units |
|---|----------------------|---------------------------|-----------|
| Operating Temperature Range | T _J | -40° ~ 125° | °Celsius |
| Maximum Thermal resistance, Junction to Case <small>Notes: 1, 3, 5</small> | R _{th-J-C} | 0.06 | °C/W |
| Maximum Thermal resistance, Case to Heat Sink <small>Notes: 1, 2, 3, 4, 5</small> | R _{th-C-HS} | 0.03 | °C/W |
| Mounting Pressure | | 450 ~ 1100 1000 ~ 2500 | kg lb. |
| <small>Note 1: Recommended mounting pressure applied. Note 2: Mounting surfaces flat and greased. Note 3: Double side cooled. Note 4: Case Temperature measured at aux., cathode. Note 5: 180° on-state</small> | | | |